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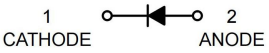
NSR0240HT1G
Schottky Barrier Diode

Schottky barrier diodes are optimized for very low forward voltage drop and low leakage current and are used in a wide range of dc−dc converter, clamping and protection applications in portable devices. NSR0240H in a SOD−323 miniature package enables designers to meet the challenging task of achieving higher efficiency and meeting reduced space requirements.

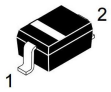
40 VOLT SCHOTTKY BARRIER DIODE



Features

- Very Low Forward Voltage Drop −480 mV @ 100 mA
- Low Reverse Current − 0.2 μA @ 25 V VR
- 250 mA of Continuous Forward Current
- Power Dissipation of 160 mW with Minimum Trace
- Very High Switching Speed
- Low Capacitance − CT = 4 pF
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

MARKING DIAGRAM



SOD−323
CASE 477
STYLE 1



AC = Specific Device Code
M = Date Code
▪ = Pb−Free Package
(Note: Microdot may be in either location)

Typical Applications

- LCD and Keypad Backlighting
- Camera Photo Flash
- Buck and Boost dc−dc Converters
- Reverse Voltage and Current Protection
- Clamping & Protection

Markets

- Mobile Handsets
- MP3 Players
- Digital Camera and Camcorders
- Notebook PCs and PDAs
- GPS

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	40	Vdc
Forward Continuous Current (DC)	I_F	250	mA
Non−Repetitive Peak Forward Surge Current	I_{FSM}	1.0	A
ESD Rating: Human Body Model Machine Model	ESD	Class 1B Class A	

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THERMAL CHARACTERISTICS

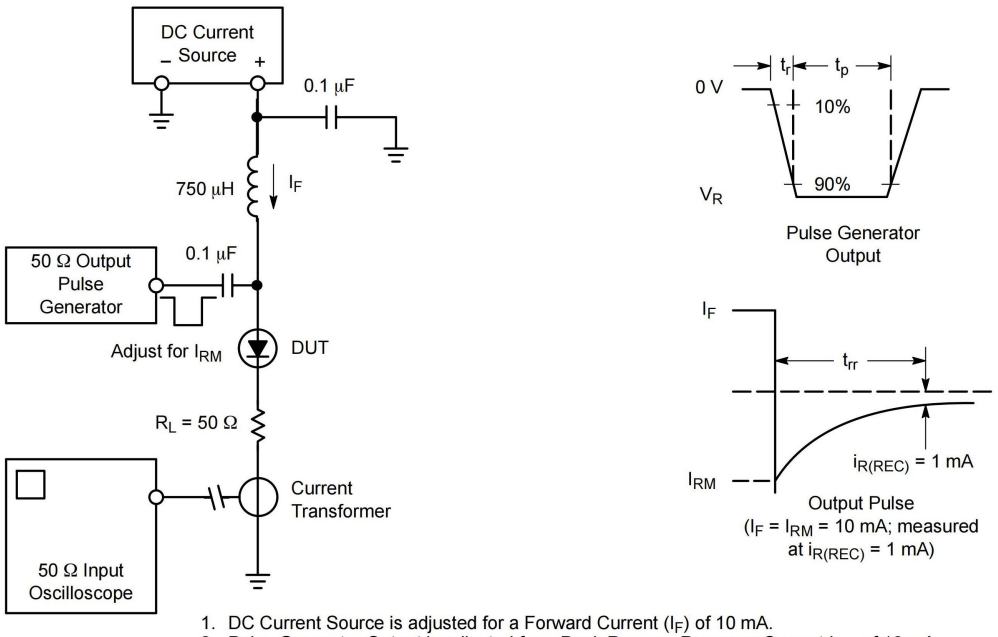
Characteristic	Symbol	Max	Unit
Thermal Resistance Junction−to−Ambient (Note 1) Total Power Dissipation @ T_A = 25°C	 $R_{\theta JA}$ P_D	 740 160	 °C/W mW
Thermal Resistance Junction−to−Ambient (Note 2) Total Power Dissipation @ T_A = 25°C	 $R_{\theta JA}$ P_D	 460 270	 °C/W mW
Junction and Storage Temperature Range	T_J, T_{stg}	−55 to +150	°C

1. Mounted onto a 4 in square FR−4 board 10 mm sq. 1 oz. Cu 0.06” thick single−sided. Operating to steady state.
2. Mounted onto a 4 in square FR−4 board 1 in sq. 1 oz. Cu 0.06” thick single−sided. Operating to steady state.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Leakage (V_R = 10 V) (V_R = 25 V) (V_R = 40 V)	I_R		 0.2 0.6	 0.55 2.0 10	μA
Forward Voltage (I_F = 10 mA) (I_F = 100 mA) (I_F = 200 mA)	V_F		 345 480 585	 450 550 710	mV
Total Capacitance (V_R = 5.0 V, f = 1 MHz)	CT		 4.0		pF
Reverse Recovery Time (I_F = I_R = 10 mA, I_R = 1.0 mA)	t_{rr}		 3.0		ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



1. DC Current Source is adjusted for a Forward Current (I_F) of 10 mA.
2. Pulse Generator Output is adjusted for a Peak Reverse Recovery Current I_{RM} of 10 mA.
3. Pulse Generator transition time << t_{rr}.
4. IR(REC) is measured at 1 mA. Typically 0.1 X I_{RM} or 0.25 X I_{RM}.
5. t_p » t_{rr}

Figure 1. Recovery Time Equivalent Test Circuit

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TYPICAL CHARACTERISTICS

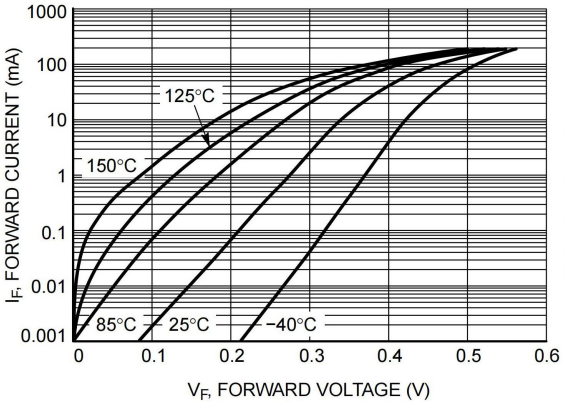

Figure 2. Forward Voltage

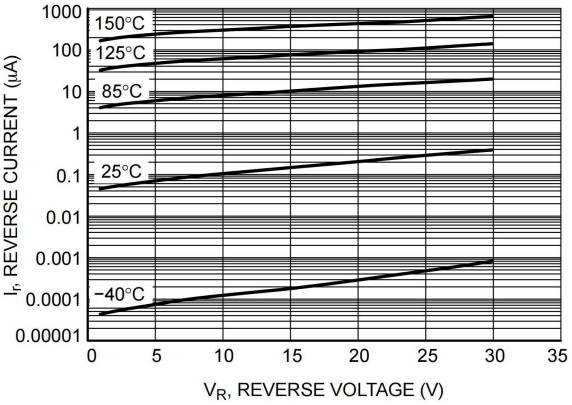

Figure 3. Leakage Current

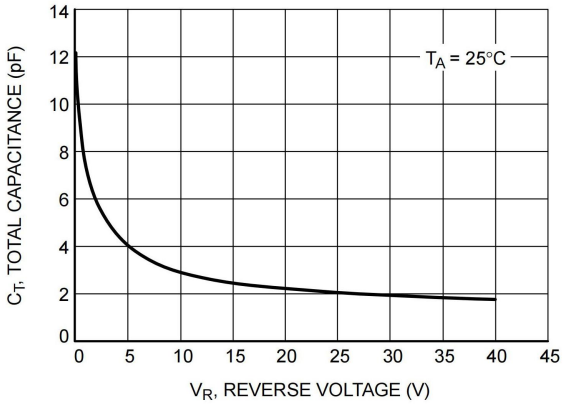

Figure 4. Total Capacitance

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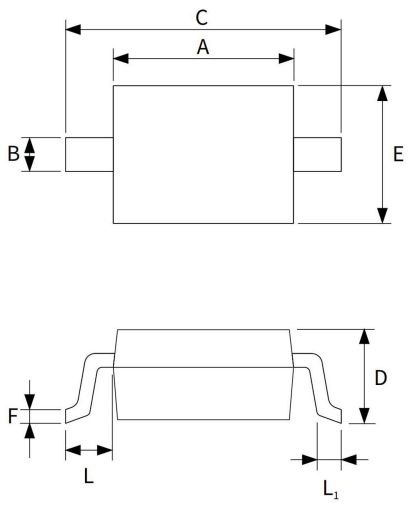
Ordering Information

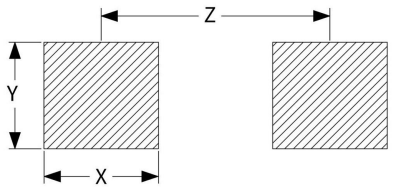
PACKAGE	PACKAGE CODE	UNIT WEIGHT(g)	REEL(pcs)	BOX(pcs)	CARTON(pcs)	DELIVERY MODE
SOD-323	R1	0.0048	3000	30000	240000	7''

Package Outline Dimensions (SOD-323)



Symbol	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	1.60	1.80	0.063	0.071
B	0.25	0.40	0.010	0.016
C	2.30	2.80	0.091	0.110
D	0.80	1.10	0.031	0.043
D_1	0.80	0.90	0.031	0.035
E	1.20	1.40	0.047	0.055
F	0.08	0.18	0.003	0.007
L	0.475REF		0.019REF	
L_1	0.25	0.40	0.010	0.016
H	-	0.14	-	0.006

Suggested Pad Layout



Symbol	Dimensions			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
X	0.65	0.75	0.026	0.030
Y	0.65	0.75	0.026	0.030
Z	2.10	2.20	0.084	0.088